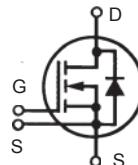


HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

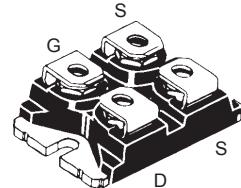
IXFN 20N120

$V_{DSS} = 1200 \text{ V}$
 $I_{D25} = 20 \text{ A}$
 $R_{DS(on)} = 0.75 \Omega$
 $t_{rr} \leq 300 \text{ ns}$



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	1200	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_c = 25^\circ\text{C}$, Chip capability	20	A
I_{DM}	$T_c = 25^\circ\text{C}$, pulse width limited by T_{JM}	80	A
I_{AR}	$T_c = 25^\circ\text{C}$	10	A
E_{AR}	$T_c = 25^\circ\text{C}$	40	mJ
E_{AS}	$T_c = 25^\circ\text{C}$	2	J
dv/dt	$I_s \leq I_{DM}$, $dI/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_c = 25^\circ\text{C}$	780	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500 3000	V~
M_d	Mounting torque Terminal connection torque	1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
Weight		30	g

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate D = Drain
S = Source TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard package
- miniBLOC, with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

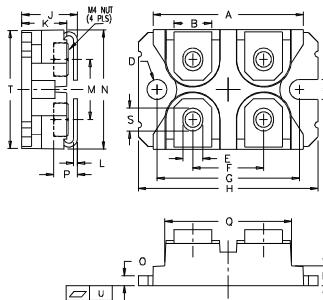
- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	1200		V
$V_{GH(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			0.75 Ω

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$V_{DS} = 20 \text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	15	27	S	
C_{iss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	7400	pF		
C_{oss}		560	pF		
C_{rss}		100	pF		
$t_{d(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1 \Omega$ (External),	25	ns		
t_r		45	ns		
$t_{d(off)}$		75	ns		
t_f		20	ns		
$Q_{g(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$	160	nC		
Q_{gs}		35	nC		
Q_{gd}		60	nC		
R_{thJC}			0.16	K/W	
R_{thCK}			0.05	K/W	

miniBLOC, SOT-227 B


M4 screws (4x) supplied

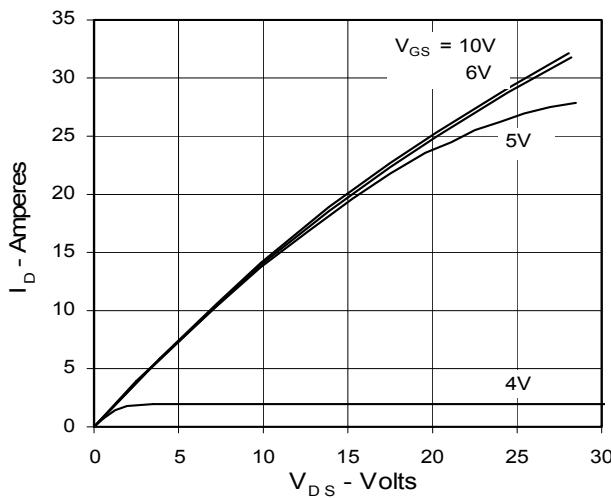
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Source-Drain Diode
Characteristic Values
 $(T_J = 25^\circ\text{C}$, unless otherwise specified)

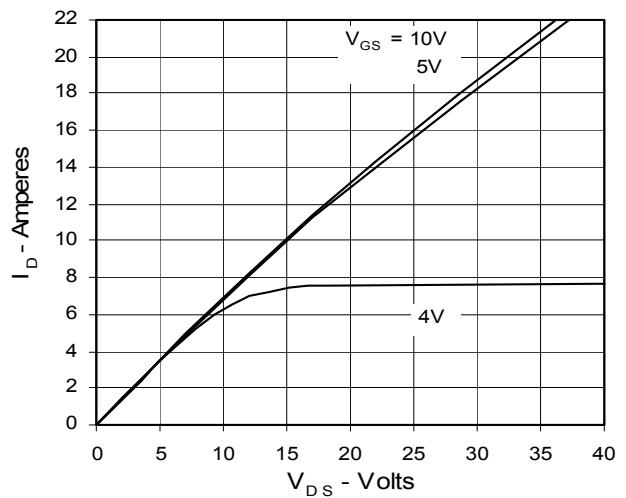
Symbol	Test Conditions	min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$		20	A
I_{SM}	Repetitive; pulse width limited by T_{JM}		80	A
V_{SD}	$I_F = I_S, V_{GS} = 0 \text{ V}$, Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		1.5	V
t_{rr}	$I_F = I_S, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100 \text{ V}$	1.4 8	300	ns
Q_{RM}			μC	
I_{RM}			A	

IXYS reserves the right to change limits, test conditions, and dimensions.

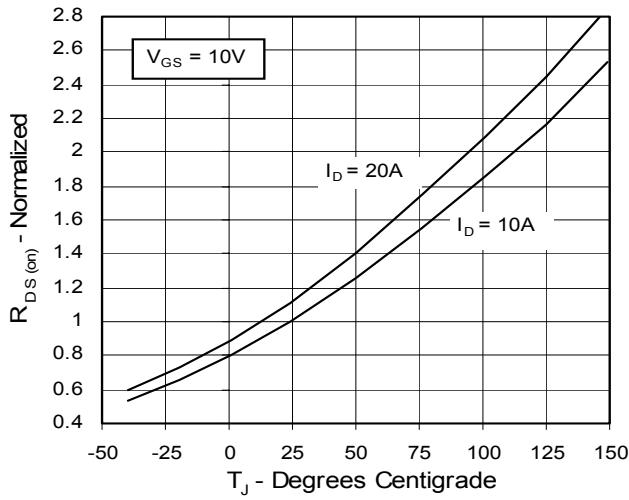
**Fig. 1. Output Characteristics
@ 25 deg. C**



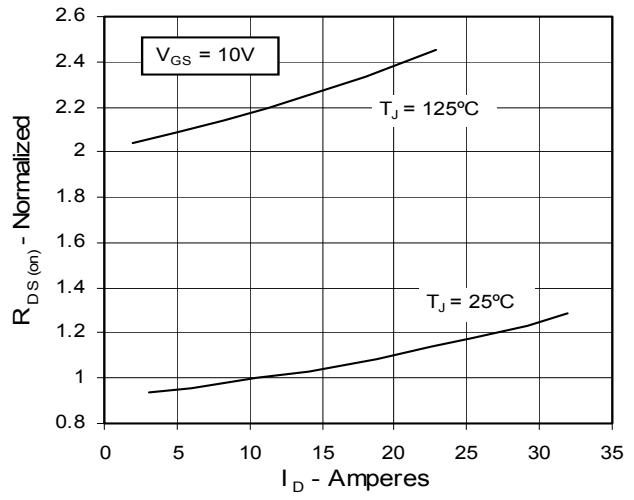
**Fig. 2. Output Characteristics
@ 125 Deg. C**



**Fig. 3. $R_{DS(on)}$ Normalized to I_{D25} Value vs.
Junction Temperature**



**Fig. 4. $R_{DS(on)}$ Normalized to I_{D25}
Value vs. I_D**



**Fig. 5. Drain Current vs. Case
Temperature**

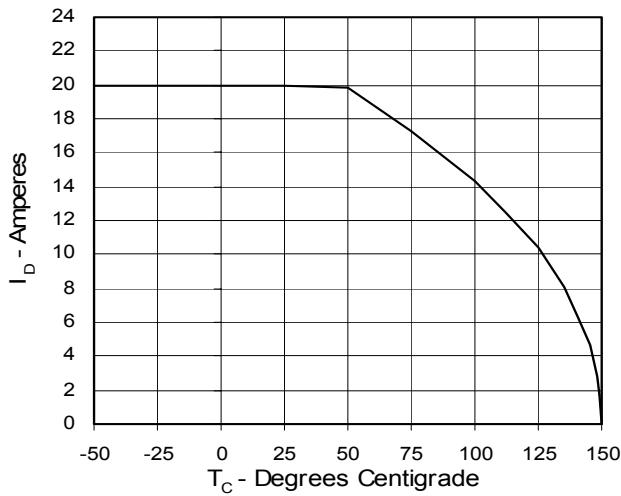


Fig. 6. Input Admittance

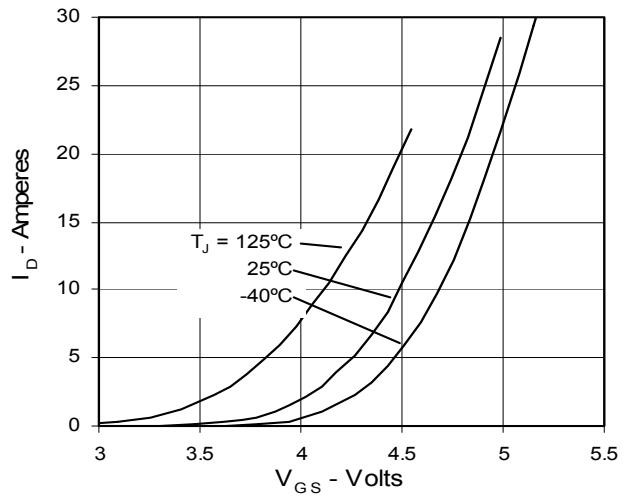


Fig. 7. Transconductance

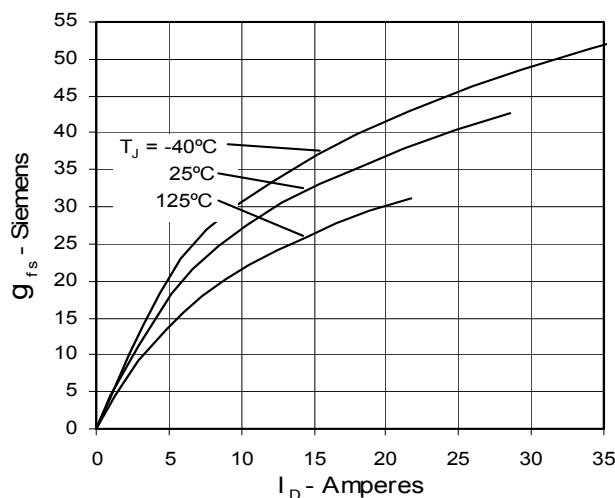


Fig. 8. Source Current vs. Source-To-Drain Voltage

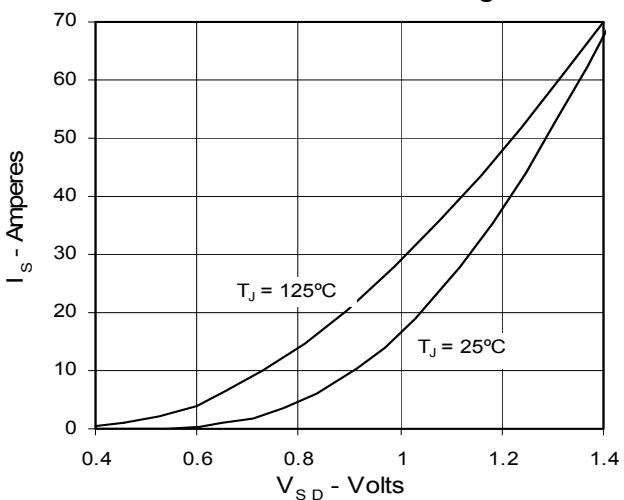


Fig. 9. Gate Charge

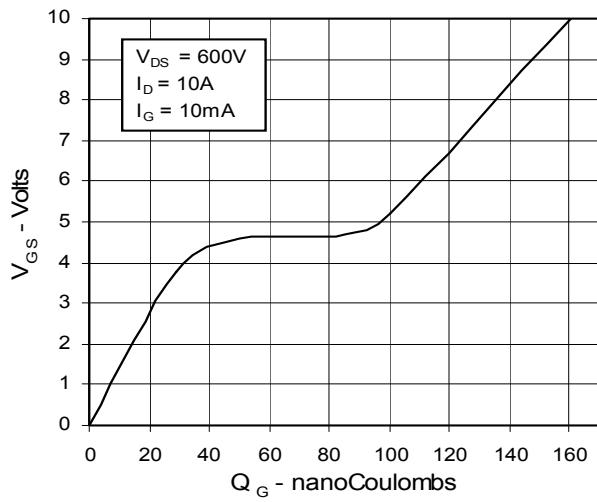


Fig. 10. Capacitance

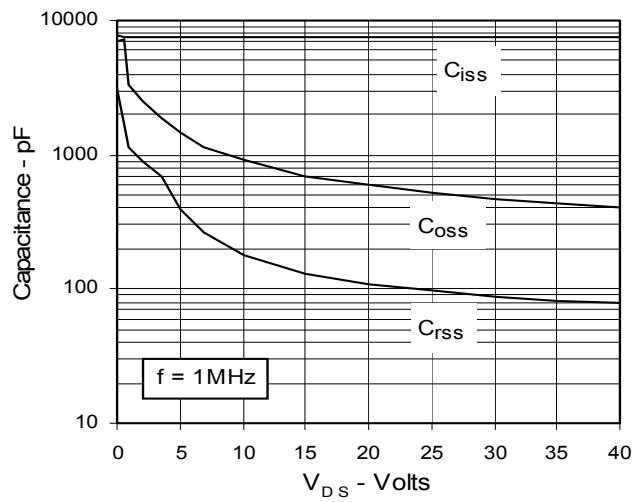
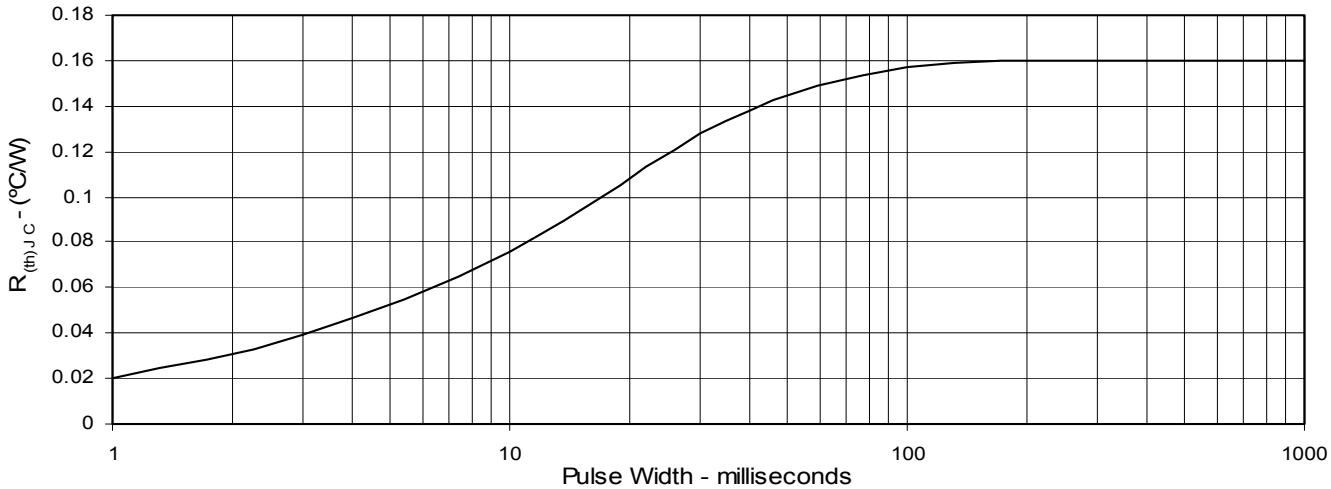


Fig. 11. Maximum Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343 6,583,505